



High Performance InGaAs p-i-n Photodiode

13PD150-S

The 13PD150-S, an InGaAs photodiode with a 150 μ m photosensitive region mounted on a metalized ceramic substrate, is intended for moderate-to-high speed applications. Efficient coupling to multi-mode fiber in hybrid modules is enabled by the relatively large photosensitive area. Planar semiconductor design and dielectric passivation provide low noise performance. Reliability is assured by a 100% purge burn-in (200°C, 15 hours, $V_r = 20V$). Chips can also be attached and wire bonded to customer-supplied or other specified submounts.

Features

Planar Structure
Dielectric Passivation
100% Purge Burn-In
High Responsivity

Device Characteristics						
Parameters	Test Conditions	Min	Typ	Max	Units	
Operating Voltage	-	-	-	-20	Volts	
Dark Current	-5V	-	0.5	2.5	nA	
Capacitance	-5V	-	1.25	2	pF	
Responsivity	1300nm	0.70	0.90	-	A/W	
Rise/Fall	-	-	-	2	ns	
Absolute Maximum Ratings						
Reverse Voltage						20 Volts
Forward Current						5 mA
Reverse Current						1 mA
Operating Temperature						-40°C to + 85°C
Storage Temperature						-40°C to + 85°C
Soldering Temperature						250°C